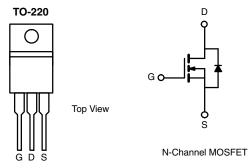


# Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	100			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0038			
I <sub>D</sub> (A)	120			
Configuration	Single			



#### **FEATURES**

- TrenchFET® Power MOSFET
- · Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % R<sub>a</sub> and UIS Tested
- Material categorization:
  For definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>



FREE

ORDERING INFORMATION	
Package	TO-220
Lead (Pb)-free and Halogen-free	SQP120N10-3m8-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	100		
Gate-Source Voltage		$V_{GS}$	± 20	V	
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	-	120		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	102		
Continuous Source Current (Diode Conduction) <sup>a</sup>		Is	120	Α	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	480		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	73		
Single Pulse Avalanche Energy	L = 0.1 IIII	E <sub>AS</sub>	266	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	В	250	W	
	T <sub>C</sub> = 125 °C	$P_D$	83	VV	
Operating Junction and Storage Temperature Ra	nge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient F	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/M	
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.6	°C/W	

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq 300 \ \mu s$ , duty cycle  $\leq 2 \ \%$ .
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static						L		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		3.0	3.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V	=	-	1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 125 °C	=	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 175 °C	=	-	500		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	120	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A	=	0.0030	0.0038		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C	=	-	0.0064	Ω	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 20 A, T <sub>J</sub> = 175 °C	=	-	0.0080		
Forward Transconductance <sup>b</sup>	9fs	V <sub>DS</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		82	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	5780	7230		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>GS</sub> = 0 V V <sub>DS</sub> = 25 V, f = 1 MHz		3070	3840	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	305	385	1	
Total Gate Charge <sup>c</sup>	Qg			=	125	190		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 50 \text{ V}, I_{D} = 70 \text{ A}$	-	28	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		=	46	-		
Gate Resistance	$R_g$		f = 1 MHz		3.3	5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		$V_{DD} = 50 \text{ V}, R_{L} = 0.7 \Omega$		16	25		
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =			110	165	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 70 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	40	60	115	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	12	20		
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>				•			
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	480	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 100 A, V <sub>GS</sub> = 0		_	0.9	1.5	V	

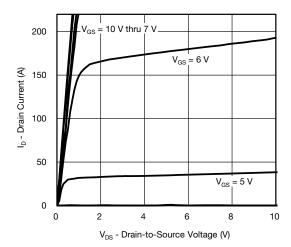
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

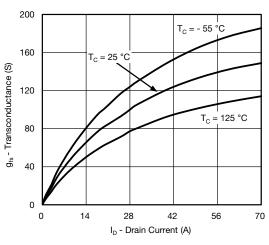
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



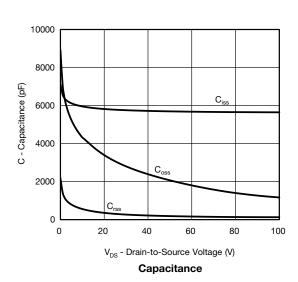
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

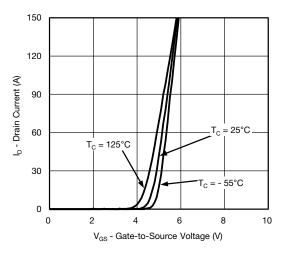


#### **Output Characteristics**

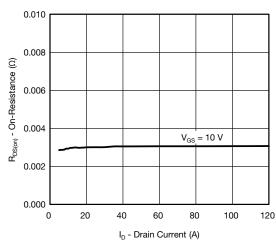


#### Transconductance

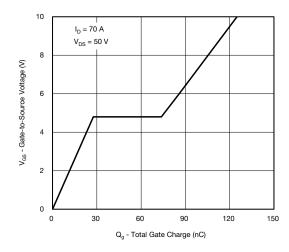




#### **Transfer Characteristics**



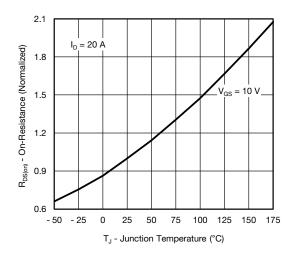
#### On-Resistance vs. Drain Current



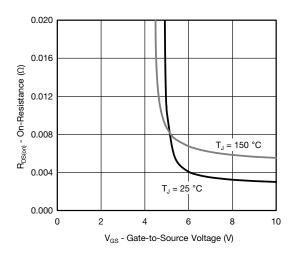
**Gate Charge** 



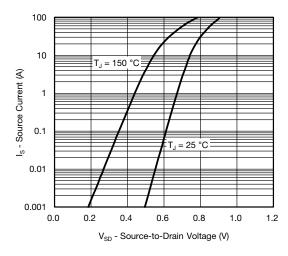
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



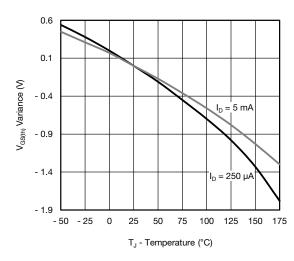
#### On-Resistance vs. Junction Temperature



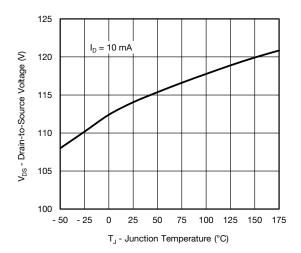
On-Resistance vs. Gate-to-Source Voltage



#### **Source Drain Diode Forward Voltage**



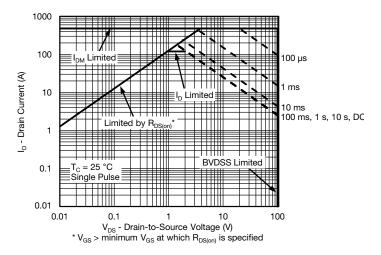
#### Threshold Voltage



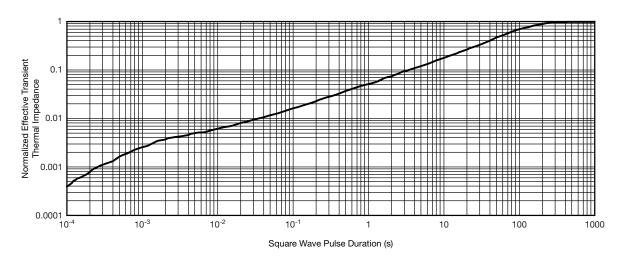
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)

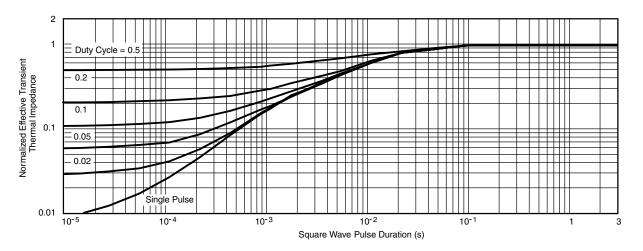


#### Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



#### Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

can widely vary depending on actual application parameters and operating conditions.

- Normalized Transient Thermal Impedance Junction to Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities

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## **TO-220AB**



	D2

	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	4.25	4.65	0.167	0.183	
b	0.69	1.01	0.027	0.040	
b(1)	1.20	1.73	0.047	0.068	
С	0.36	0.61	0.014	0.024	
D	14.85	15.49	0.585	0.610	
D2	12.19	12.70	0.480	0.500	
Е	10.04	10.51	0.395	0.414	
е	2.41	2.67	0.095	0.105	
e(1)	4.88	5.28	0.192	0.208	
F	1.14	1.40	0.045	0.055	
H(1)	6.09	6.48	0.240	0.255	
J(1)	2.41	2.92	0.095	0.115	
L	13.35	14.02	0.526	0.552	
L(1)	3.32	3.82	0.131	0.150	
ØΡ	3.54	3.94	0.139	0.155	
Q	2.60	3.00	0.102	0.118	
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471					

#### Note

 $<sup>^{\</sup>star}$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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